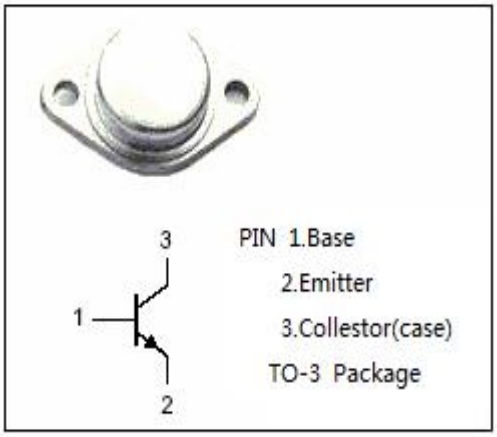
isc Silicon NPN Power Transistor — BUX10A

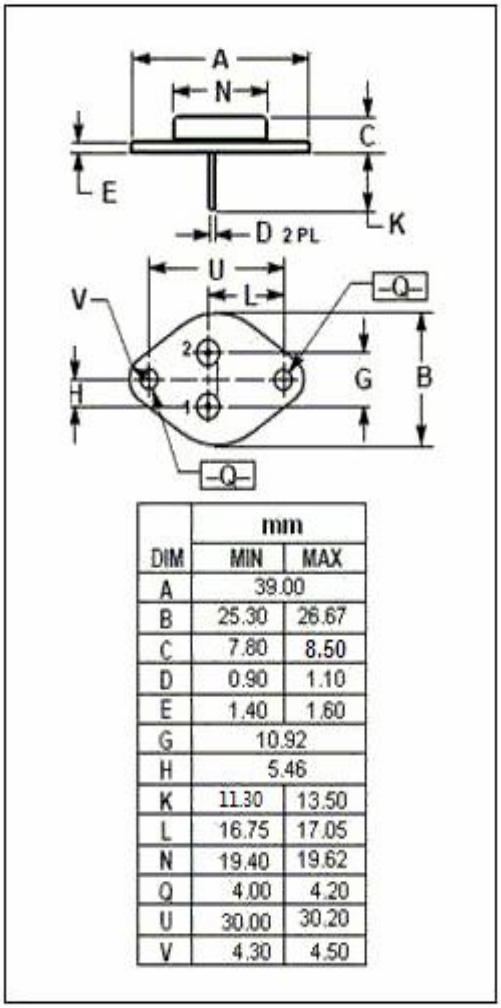
DESCRIPTION

- High Switching Speed
- High Current Capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for control amplifiers and power switching circuits, such as converters, inverters, switching regulators, and switching-control amplifiers.



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	170	V
V_{CER}	Collector-Emitter Voltage R_{BE}= 100Ω	160	V
V_{CEX}	Collector-Emitter Voltage V_{BE}= -1.5V	170	V
V_{CEO}	Collector-Emitter Voltage	125	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	25	A
I_{CM}	Collector Current-Peak	30	A
I_B	Base Current-Continuous	5	A
P_C	Collector Power Dissipation @T_C=25℃	150	W
T_j	Junction Temperature	200	℃
T_{stg}	Storage Temperature Range	-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.17	℃/W

isc Silicon NPN Power Transistor BUX10A

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 50mA; I_B= 0	125			V
$V_{CBO(SUS)}$	Collector-Base Sustaining Voltage	I_C= 1mA; I_B= 0	160			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA; I_C= 0	7			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 10A; I_B= 1A			0.6	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 20A; I_B= 2A			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 20A; I_B= 2A			2.0	V
I_{CEO}	Collector Cutoff Current	V_{CE}= 125V; I_B= 0			5.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			1.0	mA
h_{FE-1}	DC Current Gain	I_C= 10A; V_{CE}= 2V	20		70	
h_{FE-2}	DC Current Gain	I_C= 20A; V_{CE}= 4V	10			